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# LCDP1511D

# Application Specific Discretes A.S.D.<sup>TM</sup>

**DUAL LINE PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION** 

#### **FEATURES**

■ Dual line programmable transient suppressor

■ Wide negative firing voltage range: V<sub>MGL</sub> = -80V

■ Low dynamic switching voltages: V<sub>FP</sub> and V<sub>DGL</sub>

■ Low gate triggering current : I<sub>GT</sub> = 5mA max

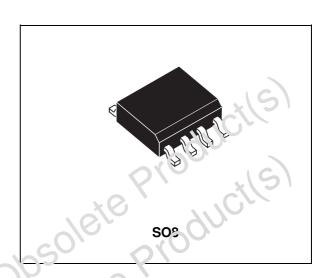
■ Peak pulse current :  $I_{PP} = 15 \text{ A} (10/1000 \, \mu\text{s})$ 

■ Holding current : I<sub>H</sub> > 150 mA

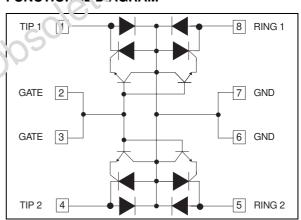
#### **DESCRIPTION**

The LCDP1511D is a dual line protector which protects subscriber line interface circuits (SLIC) against transient overvoltages.

Positive overvoltages are clamped with diodes towards GND, while negative overvoltages are suppressed by thyristors connected to GND. The breakdown voltage of the thyristors is determined by the voltage applied to the gate, generally - /bat.



#### FUNCTIONAL LYAGRAM



pressed by thyristors connected to GND. The breakdown voltage of the thyristors is determined								
I	by the voltage applied to the gate	e, generally - /	bat. TIP 1			8 RING 1		
	0,00/	CILL	GATE	2		7 GND		
		,(5)		+	•	•		
	×8,	CIL	GATE	3		6 GND		
	osolele Prodi		TIP 2		+			
	76							
	COMPLIES WITH THE FULLOWING STANDARDS:	Peak Surge Voltage (V)	Voltage Waveform (μs)	Current Waveform (µs)	Admissible Ipp	Necessary Resistor (Ω)		
0		Voltage	Waveform	Current Waveform	lpp	Necessary Resistor		
0	FOLCWING STANDARDS:	Voltage (V)	<b>Waveform</b> (μs)	Current Waveform (μs)	lpp (A)	Necessary Resistor		
0	FULCWING STANDARDS:	<b>Voltage</b> (V) 1000	<b>Waveform</b> (μs) 10/700	Current Waveform (µs) 5/310	<b>Ipp</b> (A) 25	Necessary Resistor (Ω)		
0	TIU-T K20 VDE0433	Voltage (V) 1000 2000	Waveform (μs) 10/700 10/700	Current Waveform (μs) 5/310 5/310	lpp (A) 25 25	Necessary Resistor (Ω)		
0	VDE0878	Voltage (V) 1000 2000 1500 level 2	Waveform (μs) 10/700 10/700 1.2/50 10/700	Current Waveform (μs) 5/310 5/310 1/20 5/310	lpp (A) 25 25 40 25	Necessary Resistor (Ω)		

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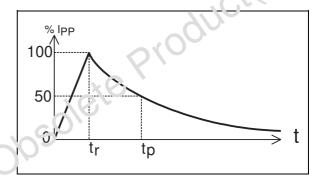
# LCDP1511D

## **ABSOLUTE MAXIMUM RATINGS** $(T_{amb} = 25^{\circ}C)$ .

Symbol	Parameter	Value	Unit		
Ірр	Peak pulse current (see note1)	urrent (see note1) 10/1000μs 5/310μs 2/10μs			
I <sub>FSM</sub>	Non repetitive surge peak on-state current (see note2)	5 3.5	Α		
V <sub>MLG</sub> V <sub>MGL</sub>	Maximum voltage LINE/GND Maximum voltage GATE/LINE		80 80	V	
T <sub>stg</sub>	Storage temperature range		- 55 to + 150	°C	
TL	Lead temperature for soldering during 10s		260	C°C;	

Note 1: Pulse waveform  $10 \, / \, 1000 \, \mu s \qquad tr = 10 \, \mu s$  $tp = 1000 \, \mu s$ 5/310 μs  $tr = 5 \mu s$  $tp = 310 \,\mu s$  $2/10\,\mu s$  $tr = 2 \mu s$  $tp = 10 \mu s$ 

Note 2: Maximum current flowing through the 4 wires together.

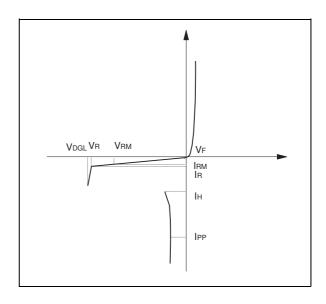


#### THERMAL RESISTANCE

Symbol	Farameter	Value	Unit
Rth (j-a)	Junction to ambient	170	°C/W

# ELECTRICAL CHA? ACTERISTICS (Tamb = 25°C)

Symbol	Parameter
IgT	Cate triggering current
Ci)	Holding current
I <sub>RM</sub>	Reverse leakage current LINE / GND
I <sub>RG</sub>	Reverse leakage current GATE / LINE
V <sub>RM</sub>	Reverse voltage LINE / GND
V <sub>GT</sub>	Gate triggering voltage
VF	Forward drop voltage LINE / GND
V <sub>FP</sub>	Peak forward voltage
V <sub>DGL</sub>	Dynamic switching voltage GATE / LINE
V <sub>GATE</sub>	GATE / GND voltage
V <sub>RG</sub>	Reverse voltage GATE / LINE
С	Capacitance LINE / GND



#### PARAMETERS RELATED TO THE DIODE LINE / GND (Tamb = 25°C)

Symbol		Test conditions				
VF	Square pulse	: $t_p = 500 \mu s$ $I_F =$	1A		2	V
V <sub>FP</sub> (note 1)	10/700μs 1.2/50μs 2/10μs	1kV 1.5kV 2.5kV	$R_P = 60\Omega$ $R_P = 60\Omega$ $R_P = 245\Omega$	IPP = 10A IPP = 15A IPP = 10A	5 10 20	V

note 1 : see test circuit for VFP, RP is the protection resistor located on the line card

#### PARAMETERS RELATED TO THE PROTECTION THYRISTOR (T<sub>amb</sub> = 25°C)

Symbol	Test co	onditions	Min	Max	Unit	
I <sub>GT</sub>	V <sub>GND / LINE</sub> = -48V				5	C <sub>1N</sub> )
lн	V <sub>GATE</sub> = -48V (see note 2	150	1.101	mA		
V <sub>GT</sub>	at I <sub>GT</sub>				2).5	V
I <sub>RG</sub>	V <sub>RG</sub> = -75V			0,	5	μΑ
V <sub>DGL</sub>	V <sub>GATE</sub> = -48V (see note 10/700μs 1kV 1.2/50μs 1.5kV 2/10μs 2.5kV	$R_{P} = 60\Omega$ $R_{P} = 60\Omega$ $R_{P} = 245\Omega$	lpp = 10A lpp = 15A lpp = 1JA	lete	7 15 20	V

note 2 : see functional holding current test circuit

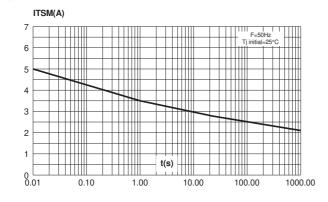
note 3 : See test circuit for VDGL
The oscillations with a time duration lower than 50ns are not taken into account

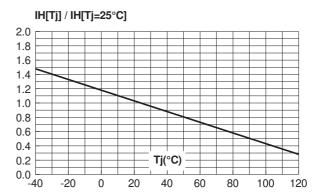
## PARAMETERS RELATED TO LINE / GISD (Tamb = 25°C)

Symbol	Test conditions	Max	Unit
I <sub>RM</sub>	V <sub>GATE / LINE</sub> = 1V V <sub>RM</sub> = -75V	5	μΑ
С	$V_R = 3V$ $= 1MHz$ $V_R = -49V$ $= 1MHz$	200 100	pF

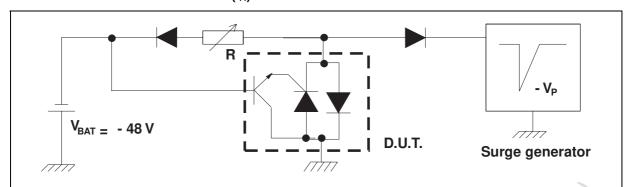
**Fiς** : Curge peak current versus overload duration.

Fig. 2: Relative variation of holding current versus junction temperature.





#### FUNCTIONAL HOLDING CURRENT (IH) TEST CIRCUIT: GO-NO GO TEST

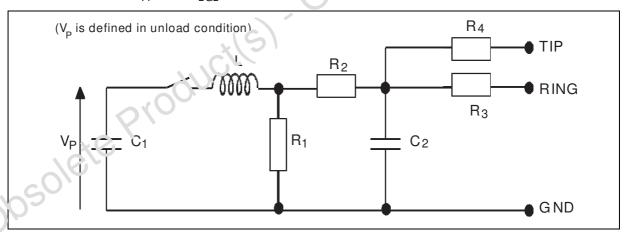


This is a GO-NO GO test which allows to confirm the holding current (I<sub>H</sub>) level in a functional test circuit.

#### **TEST PROCEDURE:**

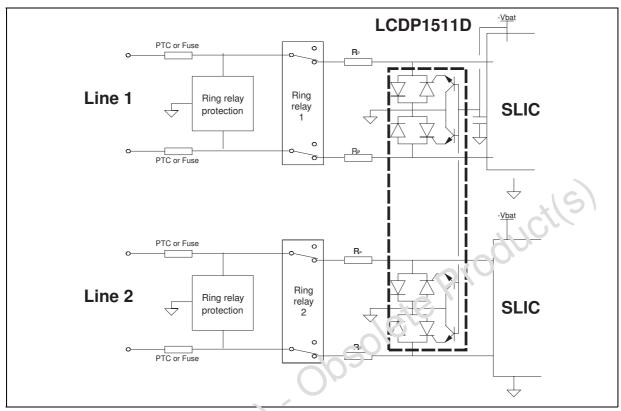
- Adjust the current level at the I<sub>H</sub> value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current: I<sub>PP</sub> = 15A, 10/1000μs.
   The D.U.T. will come back to the off-state within a duration of 50ms max.

#### TEST CIRCUIT FOR VFP AND VDGL PARAMETER'S

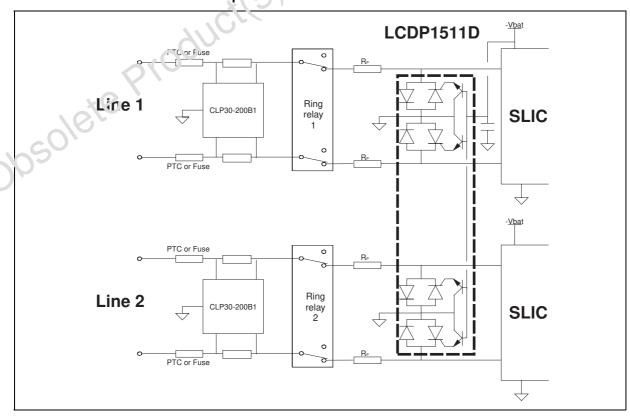


Pulse	e (μs)	Vp	C <sub>1</sub>	C <sub>2</sub>	L	R <sub>1</sub>	R <sub>2</sub>	R <sub>3</sub>	R <sub>4</sub>	IPP	Rp
tr	tp	(V)	(μF)	(nF)	(μH)	$(\Omega)$	$(\Omega)$	$(\Omega)$	$(\Omega)$	(A)	$(\Omega)$
10	700	1000	20	200	0	50	15	25	25	10	60
1.2	50	1500	1	33	0	76	13	25	25	15	60
2	10	2500	10	0	1.1	1.3	0	3	3	10	245

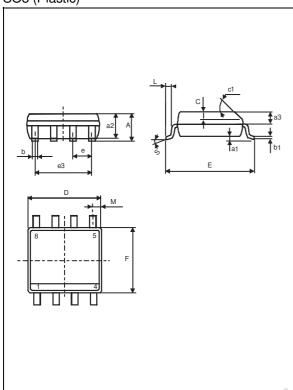
## **APPLICATION CIRCUIT: PABX line protection**



#### APPLICATION CIRCUIT: Line Card protection



# PACKAGE MECHANICAL DATA SO8 (Plastic)



	DIMENSIONS								
REF.	Mi	Millimetres			Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.			
Α			1.75			0.069			
a1	0.1		0.25	0.004		0.010			
a2			1.65			0.065			
аЗ	0.65		0.85	0.025		0.033			
b	0.35		0.48	0.014		0.019			
b1	0.19		0.25	0.007		0.010			
С	0.25	0.50	0.50	0.010	4	0.020			
c1			45°	(typ)	10				
D	4.8		5.0	0.189		0.197			
Е	5.8		6.2	0.228	5	0.244			
е		1.27		()·	0.050				
e3		3.8			0.150				
F	3.8	0.	4.0	0.15		0.157			
L	0 4		1.27	0.016		0.050			
М	710		0.6			0.024			
\$5		8° (max)							

Ordre code	Marking	Package	Weight	Base qty	Delivery mode
LCDP1511D	LCDP15	SO8	0.077 g	100	Tube
LCDP1511DRI	LCDP15	SO8	0.077 g	2500	Tape & reel

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